



# MM54HCT257/MM74HCT257 Quad 2-Channel TRI-STATE® Multiplexer

# MM54HCT258/MM74HCT258 Quad 2-Channel TRI-STATE® Multiplexer (Inverted Output)

## General Description

These Quad 2-to-1 line date selector/multiplexers utilize advanced silicon-gate CMOS technology. Along with the high noise immunity and low power dissipation of standard CMOS integrated circuits, these possess the ability to drive LS-TTL loads. The large output drive capability coupled with the TRI-STATE feature make these devices ideal for interfacing with bus lines in a bus organized system. When the OUTPUT CONTROL input line is taken high, the outputs of all four multiplexers are sent into a high impedance state. When the OUTPUT CONTROL line is low, A or B data is selected for the HCT257 while  $\bar{A}$  or  $\bar{B}$  data is selected for the HCT258.

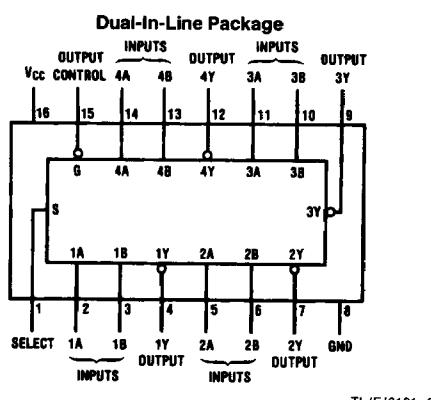
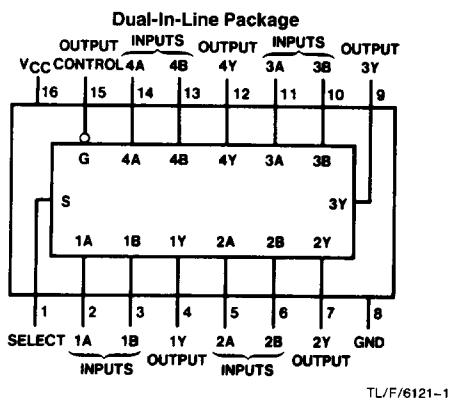
The 54HCT/74HCT logic family is speed, function, and pin-out compatible with the standard 54LS/74LS logic family.

All inputs are protected from damage due to static discharge by internal diode clamps to  $V_{CC}$  and ground.

## Features

- Typical propagation delay: 15 ns
- Power supply range: 5V  $\pm$  10%
- Low quiescent current: 80  $\mu$ A maximum (74HC Series)
- Completely TTL compatible
- TRI-STATE outputs for connection to system buses
- Added circuitry allows data input levels to float during TRI-STATE with no additional power consumption
- High output drive current: 60 mA minimum

## Connection Diagrams



Order Number MM54HCT257\* or MM74HCT257\*

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\*Please look into Section 8, Appendix D for availability of various package types.

## Truth Tables

Inputs			Output Y
Output Control	Select	A B	
H	X	X X	Z
L	L	L X	L
L	L	H X	H
L	H	X L	L
L	H	X H	H

H = high level, L = low level, X = irrelevant, Z = high impedance, (off)

Inputs			Output Y
Output Control	Select	A B	
H	X	X X	Z
L	L	L X	H
L	L	H X	L
L	H	X L	H
L	H	X H	L

**Absolute Maximum Ratings** (Notes 1 & 2)

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage ( $V_{CC}$ )	-0.5V to +7.0V
DC Input Voltage ( $V_{IN}$ )	-1.5V to $V_{CC}$ + 1.5V
DC Output Voltage ( $V_{OUT}$ )	-0.5V to $V_{CC}$ + 0.5V
Clamp Diode Current ( $I_{IK}, I_{OK}$ )	$\pm 20$ mA
DC Output Current, per Pin ( $I_{OUT}$ )	$\pm 35$ mA
DC $V_{CC}$ or GND Current, per Pin ( $I_{CC}$ )	$\pm 70$ mA
Storage Temperature Range ( $T_{STG}$ )	-65°C to +150°C
Power Dissipation ( $P_D$ ) (Note 3)	600 mW
S.O. Package only	500 mW
Lead Temp. ( $T_L$ ) (Soldering, 10 sec.)	260°C

**Operating Conditions**

	Min	Max	Units
Supply Voltage ( $V_{CC}$ )	2	6	V
DC Input or Output Voltage ( $V_{IN}, V_{OUT}$ )	0	$V_{CC}$	V
Operating Temp. Range ( $T_A$ )			
MM74HCT	-40	+85	°C
MM54HCT	-55	+125	°C
Input Rise or Fall Times ( $t_r, t_f$ )	$V_{CC} = 4.5V$		
		500	ns

**DC Electrical Characteristics** (Note 4)  $V_{CC} = 5V \pm 10\%$ 

Symbol	Parameter	Conditions	$T_A = 25^\circ C$		<b>74HCT</b>	<b>54HCT</b>	Units
			Typ		$T_A = -40^\circ C$ to $85^\circ C$	$T_A = -55^\circ C$ to $125^\circ C$	
$V_{IH}$	Minimum High Level Input Voltage			3.15	3.15	3.15	V
$V_{IL}$	Maximum Low Level Input Voltage			0.9	0.9	0.9	V
$V_{OH}$	Minimum High Level Output Voltage	$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 20 \mu A$	4.5	4.4	4.4	4.4	V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 6.0$ mA, $V_{CC} = 4.5V$ $ I_{OUT}  \leq 7.2$ mA, $V_{CC} = 5.5V$	4.2	3.98 4.98	3.84 4.84	3.7 4.7	V
$V_{OL}$	Maximum Low Level Output Voltage	$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 20 \mu A$	0	0.1	0.1	0.1	V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 6.0$ mA, $V_{CC} = 4.5V$ $ I_{OUT}  \leq 7.2$ mA, $V_{CC} = 5.5V$	0.2	0.26 0.26	0.33 0.33	0.4 0.4	V
$I_{IN}$	Maximum Input Current	$V_{IN} = V_{CC}$ or GND		$\pm 0.1$	$\pm 1.0$	$\pm 1.0$	$\mu A$
$I_{OZ}$	Maximum TRI-STATE Output Leakage	$V_{OUT} = V_{CC}$ or GND $OC = V_{IH}$		$\pm 0.5$	$\pm 5.0$	$\pm 10$	$\mu A$
$I_{CC}$	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$		8.0	80	160	$\mu A$
		$V_{IN} = 2.4V$ or $0.5V$ (Note 4)		1.2	1.4	1.5	mA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of  $5V \pm 10\%$  the worst case output voltages ( $V_{OH}$  and  $V_{OL}$ ) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case  $V_{IH}$  and  $V_{IL}$  occur at  $V_{CC} = 5.5V$  and 4.5V respectively. (The  $V_{IH}$  value at 5.5V is 3.85V.) The worst case leakage current ( $I_{IN}$ ,  $I_{CC}$ , and  $I_{OZ}$ ) occur for CMOS at the higher voltage and so the 6.0V values should be used.

**AC Electrical Characteristics**  $V_{CC} = 5V$ ,  $T_A = 25^\circ C$ ,  $C_L = 45 pF$ ,  $t_r = t_f = 6 ns$  (unless otherwise noted)

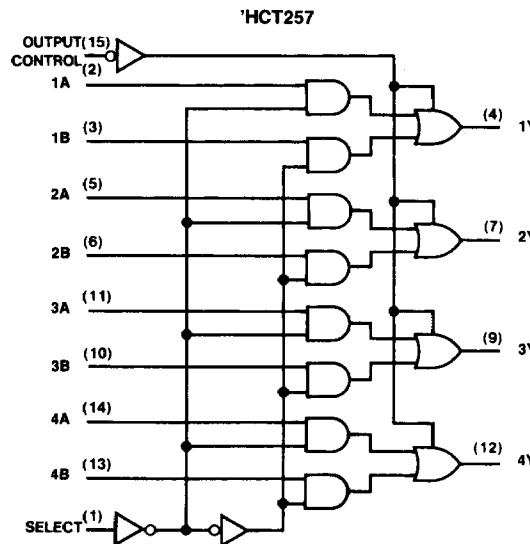
Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
$t_{PHL}, t_{PLH}$	Maximum Propagation Select to any Output		16		ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay A or B to any Output		12		ns
$t_{PZH}, t_{PZL}$	Maximum Enable Time	$R_L = 1 k\Omega$	23		ns
$t_{PHZ}, t_{PLZ}$	Maximum Disable Time	$R_L = 1 k\Omega$ $C_L = 5 pF$	8		ns

**AC Electrical Characteristics**  $V_{CC} = 5V \pm 10\%$ ,  $t_r = t_f = 6 ns$ ,  $C_L = 50 pF$  (unless otherwise noted)

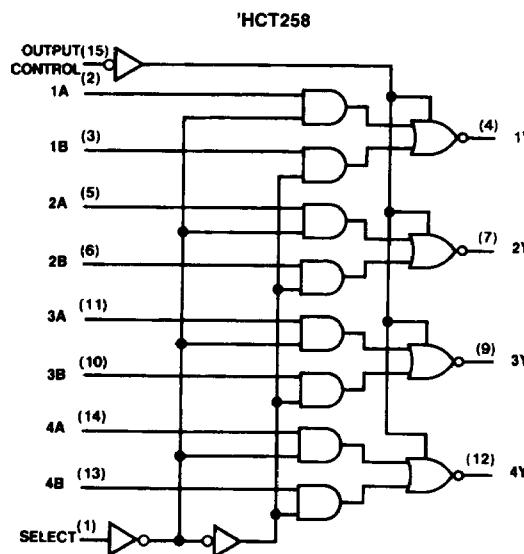
Symbol	Parameter	Conditions	$T_A = 25^\circ C$		<b>74HCT</b>	<b>54HCT</b>	Units
			Typ	Guaranteed Limits			
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, Select to any Output		18	24	30	36	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, A or B to any Output		15	20	25	30	ns
$t_{PZH}, t_{PZL}$	Maximum Enable to any Output	$R_L = 1k$ $C_L = 50 pF$		34	43	51	ns
$t_{PHZ}, t_{PLZ}$	Maximum Disable Time	$R_L = 1k$ $C_L = 50 pF$	15	21	26	32	ns
$t_{THL}, t_{TLH}$	Maximum Output Rise and Fall Times			12	15	18	ns
$C_{PD}$	Power Dissipation Capacitance (Note 5)		44				pF
$C_{IN}$	Maximum Input Capacitance		5	10	10	10	pF

Note 5:  $C_{PD}$  determines the no load dynamic power consumption,  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ , and the no load dynamic current consumption,  $I_S = C_{PD} V_{CC} f + I_{CC}$ .

## Logic Diagrams



TL/F/6121-3



TL/F/6121-4